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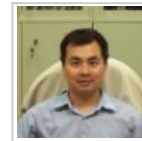
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Calendar

« August 2018 »

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Journal paper summary

出版年份	Publication	Author
2017	None , 99 , pp1-1 ,2017, (SCI)	Wen-Kuan Yeh
2017	64 , 5 , pp 2314- 2320 ,2017, (SCI)	Wen-Kuan Yeh
2016	67 , 1 , pp89-93 ,2016, (SCI)	Wen-Kuan Yeh
2016	37 , 11 , pp1379-1381, ,2016, (SCI)	Wen-Kuan Yeh
2016	16 , 4 , pp610-616 ,2016, (SCI)	Wen-Kuan Yeh
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2016	37 , 2 , pp138-141 ,2016, (SCI)	Wen-Kuan Yeh
2016	19 , 2 , pp888-893 ,2016, (SCI)	Wen-Kuan Yeh
2015	12 , 3 , pp1-4 ,2015, (SCI)	

出版年份	Publication	Author
		Wen-Kuan Yeh
2015	12 , 1/2 , pp87-89 ,2015, (SCI)	Wen-Kuan Yeh
2015	14 , 2 , pp1536-1550 ,2015, (SCI)	Wen-Kuan Yeh
2014	W. T. Chang, C. M. Lai , W. K. Yeh,"Reliability of the Doping Concentration in an Ultra-thin Body and Buried Oxide Silicon on Insulator (SOI) and Comparison with a Partially Depleted SOI" , Microelectronics Reliability , 54 , 2 , pp485-489 ,2014, (SCI)	Wen-Kuan Yeh
2014	Yi-Lin Yang, Tzu-Sung Yen, Jia-Jian Hong(洪嘉鍵), Jie-Chen Wong(翁介辰), Chao-Chen Ku, Tai-Hsuan Wu, Tzuo-Li Wang, Chien-Yi Li, Bing-Tze Wu, Shih-Hung Lin, Wen-Kuan Yeh,"Examination of hot-carrier stress induced degradation on fin field-effect transistor" , Applied Physics Letters , 104 , 10 , pp1063-1066 ,2014, (SCI)	Wen-Kuan Yeh
2013	Cheng-Li Lin, Po-Hsiu Hsiao, Wen-Kuan Yeh, Han-Wen Liu, Syuan-Ren Yang, Yu-Ting Chen, Kun-Ming Chen,and Wen-Shiang Liao,"Effects of Fin Width on Device Performance and Reliability of Double-Gate n-Type FinFETs" , IEEE TRANSACTIONS ON ELECTRON DEVICES , 60 , 11 , pp3639-3644 ,2013, (SCI)	Wen-Kuan Yeh
2013	6 , 53 , pp878-884 ,2013, (SCI)	Wen-Kuan Yeh
2013	4 , 53 , pp265-269 ,2013, (SCI)	Wen-Kuan Yeh
2013	4 , 328 , pp669-673 ,2013, (SCI)	Wen-Kuan Yeh
2012	Yi-Lin Yang, Wenqi Zhang, Chi-Yun Cheng, Yi-Ping Huang, Pin-Tseng Chen, Chia-Wei Hsu, Li-Kong Chin, Chien-Ting Lin, Che-Hua Hsu, Chien-Ming Lai, and Wen-Kuan Yeh,"Reliability Improvement of 28-nm High-k/Metal Gate-Last MOSFET Using Appropriate Oxygen Annealing" , IEEE ELECTRON DEVICE LETTERS , 33 , 8 , pp1183-1185 ,2012, (SCI)	Wen-Kuan Yeh
2012	Wen-Kuan Yeh , Po-Ying Chen , Kwang-Jow Gan , Jer-Chyi Wang , Chao Sung Lai,"The impact of interface/border defect on performance and reliability of high-k/metal-gate CMOSFET" , Microelectronics Reliability , 10 , 2 , pp11-16 ,2012, (SCI)	Wen-Kuan Yeh
2012	H.D. Yen, J.S. Yuan, R.L. Wang, G.W. Huang, W.K. Yeh , and F.S. Huang,"RF stress effects on CMOS LC-loaded VCO reliability evaluated by experiments" , Microelectronics Reliability , 12 , 2 , pp369-374 ,2012, (SCI)	Wen-Kuan Yeh
2012	Yi-Lin Yang, Wenqi Zhang, Chi-Yun Cheng and Wen-kuan Yeh,"The Improvement of Reliability of High-k/Metal Gate pMOSFET Device with Various PMA Conditions" , Active and Passive Electronic Components , 2012 , Article ID 872494 , pp.-. ,2012, (EI)	Wen-Kuan Yeh
2012	Kwang-Jow Gan, Cher-Shiung Tsai, Kuan-Yu Chun, Wen-Kuan Yeh, and Jeng-Jong Lu,"Frequency divider design using the combination of transistors and passive devices" , Analog Integr. Circ. Sig. Process. , 70 , 1 , pp141-145 ,2012, (SCI)	Wen-Kuan Yeh
2011	Kwang-Jow Gan, Cher-Shiung Tsai, Chi-Wen Hsien, Yu-Kuang Li and Wen-Kuan Yeh,"Design of monostable-bistable transition logic element using the BiCMOS-based negative differential resistance circuit" , Analog Integr. Circ. Sig. Process , 68 , 3 , pp379-385 ,2011, (SCI)	Wen-Kuan Yeh
2011	Jiann-Shiun Yuan, Wen-Kuan Yeh, Shuyu Chen and Chia-Wei Hsu,"NBTI reliability on high-k metal-gate SiGe transistor and circuit performances" , Microelectron. Reliab. , 51 , 5 , pp914-918 ,2011, (SCI)	Wen-Kuan Yeh
2011	Cheng-Li Lin and Wen-Kuan Yeh,"Impact of SOI thickness on device performance and gate oxide reliability of Ni fully Silicide metal-gate strained SOI MOSFET" , Microelectronic Engineering , 88 , 3 , pp228-234 ,2011, (SCI)	Wen-Kuan Yeh
2011	Yu-Ting Chen, K.-M. Chen, Wen-Kuan Yeh, C.-C. Wang, C-L. Lin, J.-S. Yuan, and F.-S. Yeh,"Impact of SOI Thickness on FUSI-Gate CESL CMOS Performance and Reliability" , IEEE Transactions on Device and Materials Reliability , 11 , 1 , pp44-49 ,2011, (SCI),(EI)	Wen-Kuan Yeh
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2010	Po-Ying Chen, Ming-Hsing Tsai, Wen-Kuan Yeh, Ming-Haw Jing, and Yukon Chang, "Relationship between wafer fracture reduction and controlling during the edge manufacturing process" , Microelectronic Engineering , 87 , 10 , pp1809-1815 ,2010, (SCI)	Wen-Kuan Yeh
2010	Wen-Teng Chang, Chih-Chung Wang (王治忠), Jian-An Lin (林建安), and Wen-Kuan Yeh, "External Stresses on Tensile and Compressive Contact Etching Stop Layer SOI MOSFETs" , IEEE Transactions on Electron Devices , 57 , 8 , pp1889-1894 ,2010, (SCI), (EI)	Wen-Kuan Yeh
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2010	Cheng-Li Lin, Yu-Ting Chen, Fon-Shan Huang, Wen-Kuan Yeh, and Chien-Ting Lin, "The Impact of Oxide Traps Induced by SOI Thickness on Reliability of Fully Silicide Metal-Gate Strained SOI MOSFET" , IEEE Electron Device Letters , 31 , 2 , pp165-167 ,2010, (SCI), (EI)	Wen-Kuan Yeh
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2008	Chia-Wei Hsu, Yean-Kuen Fang, Wen-Kuan Yeh, and Chien-Ting Lin, "Significantly improving sub-90 nm CMOSFET performances with notch-gate enhanced high tensile-stress contact etch stop layer" , Microelectronics Reliability , 48 , 11-12 , pp1791-1794 ,2008, (SCI), (其他)	Wen-Kuan Yeh
2008	Po-Ying CHEN, Shen-Li CHEN, Ming-Hsing TSAI, Wen-Kuan YEH, Heng-Yu Kung, and Yu Kuan CHANG, "Elucidating the Effects of Current Stress History on Reliability Characteristics by Dynamic Analysis" , Japanese Journal of Applied Physics , 47 , 10 , pp7836-7838 ,2008, (SCI)	Wen-Kuan Yeh
2008	Chia-Wei Hsu, Yean-Kuen Fang, Chien-Ting Lin, Wen-Kuan Yeh, Che-Hua Hsu , Chieh-Ming Lai, Li-Wei Cheng, and Mike Ma, "Significant Improvement of 45nm and Beyond Complementary Metal Oxide Semiconductor Field Effect Transistor Performance with Fully Silicided and Ultimate Spacer Process Technology" , Thin Solid Films , 516 , 21 , pp7741-7743 ,2008, (SCI)	Wen-Kuan Yeh
2008	Shuo-Mao Chen , Yean-Kuen Fang , Wen-Kuan Yeh , I.C. Lee , and Yen-Ting Chiang, "A high current gain gate-controlled lateral bipolar junction transistor with 90 nm CMOS technology for future RF SoC applications" , Solid-State Electronic , 52 , 8 , pp1140-1144 ,2008, (其他)	Wen-Kuan Yeh
2008	Po-Ying Chen, Heng-yu Kung, Yi-Shao Lai, Ming Hsiung Tsai, and Wen-Kuan Yeh, "Reliability and Characteristics of Wafer-Level Chip Scale Packages under Current stress" , Japanese Journal of Applied Physics , 47 , 2 , pp819-823 ,2008, (SCI)	Wen-Kuan Yeh
2007	Wen-Kuan Yeh, "The Impact of Mobility Enhanced Technology on Device Performance and Reliability for sub-90nm SOI nMOSFETs" , Microelectronic Engineering , 84 , 9-10 , pp2077-2080 ,2007, (SCI), (其他)	Wen-Kuan Yeh
2007	Chien-Ting Lin, Yean-Kuen Fang, Wen-Kuan Yeh, Chieh-Ming Lai, Che-Hua Hsu, Li-Wei Cheng, and Guang Hwa Ma, "Impacts of Notched-Gate Structure on Contact Etch Stop ayer (CESL) Stressed 90-nm nMOSFET" , IEEE Electron Device Letters , 28 , 5 , pp376-378 ,2007, (SCI), (EI)	Wen-Kuan Yeh
2007	Chien-Ting Lin, Yean-Kuen Fang, Chieh-Ming Lai, Wen-Kuan Yeh, Che-Hua Hsu, Li-Wei Cheng, Yao-Tsung Huang, and Guang Hwa Ma, "Extra Bonus on Transistor Optimization with Stress Enhanced Notch-gate Technology for sub-90nm CMOSFET" , Japanese Journal of Applied Physics , 46 , 4B , pp2131-2133 ,2007, (SCI)	Wen-Kuan Yeh
2007	Chieh-Ming Lai, Yean-Kuen Fang, Chien-Ting Lin, and Wen-Kuan Yeh, "Efficient Mobility Enhancement Engineering on 65nm Fully Silicided complementary MOSFET Using Second Contact Etch Stop Layer Process" , Japanese Journal of Applied Physics , 46 , 4B , pp2127-2130 ,2007, (SCI)	Wen-Kuan Yeh
2007	Chien-Ting Lin, Yean-Kuen Fang, Wen-Kuan Yeh, Tung-Hsing Lee, Ming-Shing Chen, Chieh-Ming Lai, Che-Hua Hsu, Liang-Wei Chen, Li-Wei Cheng, and Mike Ma, "A Novel Strain Method for Enhancement of 90-nm Node and Beyond FUSI-	Wen-Kuan Yeh

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	Gated CMOS Performance" , IEEE Electron Device Letters , 28 , 2 , pp111-113 ,2007, (SCI),(EI)	
2007	Chieh-Ming Lai, Yean-Kuen Fang, Wen-Kuan Yeh, Chien-Ting Lin, and T. H. Chou,"The Investigation of Post-Annealing-Induced Defects Behavior on 90-nm In Halo nMOSFETs With Low-Frequency Noise and Charge-Pumping Measuring" , IEEE Electron Device Letters , 28 , 2 , pp142-144 ,2007, (SCI),(EI)	Wen-Kuan Yeh
2006	Chien-Ting Lin, Yean-Kuen Fang, Wen-Kuan Yeh, Tung-Hsing Lee, Ming-Shing Chen, Che-Hua Hsu, Liang-Wei Chen, Li-Wei Cheng, and Mike Ma,"Effect of Silicon Thickness on Contact-Etch-Stop-Layer-Induced Silicon/Buried-Oxide Interface Stress for Partially Depleted SOI " , IEEE Electron Device Letters , 27 , 12 , pp963-965 ,2006, (SCI),(EI)	Wen-Kuan Yeh
2006	Chieh-Ming Lai, Yean-Kuen Fang, Chien-Ting Lin, and Wen-Kuan Yeh , "The Geometry Effect of Contact Etch Stop Layer Impact on Device Performance and Reliability for 90-nm SOI nMOSFETs" , IEEE Transactions on Electron Devices , 53 , 11 , pp2779-2785 ,2006, (SCI)	Wen-Kuan Yeh
2006	Chieh-Ming Lai, Yean-Kuen Fang, Wen-Kuan Yeh, S. H. Chen, and Ta-Hsun Yeh,"Stress Technology Impact on Device Performance and Reliability for <100> sub-90nm SOI CMOSFETs" , Japanese Journal of Applied Physics , 45 , 4B , pp3053-3057 ,2006, (SCI)	Wen-Kuan Yeh
2006	Chien-Ting Lin, Yean-Kuen Fang, Wen-Kuan Yeh, Tung-Hsing Lee, Ming-Hing Chen, C. H. Hsu, L. W. Chen, H. C. Chang, C. T. Tsai, and M. Ma,"Investigation and Modeling of Stress Interactions on 90 nm SOI CMOS with Various Mobility Enhancement Approaches" , Japanese Journal of Applied Physics , 45 , 4B , pp3049-3052 ,2006, (SCI)	Wen-Kuan Yeh
0000	PP , 99 , pp1-1 , (SCI)	Wen-Kuan Yeh
0000	PP , 99 , pp1-1 , (SCI)	Wen-Kuan Yeh
0000	12 , 3 , pp1-4 , (SCI)	Wen-Kuan Yeh

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Educational background summary

School name	Country	Department	Degree	Starting date
				1992-07 ~ 1996-04

Experiences

Service organization/unit	Job title	Department	Responsibilities	Starting date
				2010 ~
				2009 ~ 2010
				2006 ~ 2009
				2005 ~
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